

Ted Johansson, LIST OF PUBLICATIONS AND PATENTS

updated 2018-11-25

1 REGULAR PAPERS (peer-reviewed)

1. H. Norström, S. Nygren, T. Johansson, R. Buchta, M. Östling, A. Lindberg, U. Gustafsson, C. S. Petersson, "A Refined Polycide Gate Process With Silicided Diffusions for Submicron MOS Applications", *J. Electrochem. Soc.*, 136, 805 (1989).
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